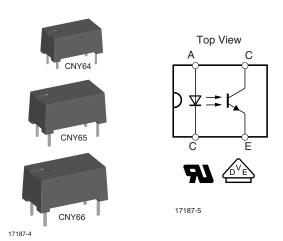


Vishay Semiconductors

# Optocoupler, Phototransistor Output, Very High Isolation Voltage



#### **DESCRIPTION**

The CNY64, CNY65, and CNY66 consist of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 4 pin plastic package.

The single components are mounted opposite one another, providing a distance between input and output for highest safety requirements of > 3 mm.

#### **VDE STANDARDS**

These couplers perform safety functions according to the following equipment standards:

- DIN EN 60747-5-2 (VDE 0884)
   Optocoupler for electrical safety requirements
- IEC 60950/EN 60950 Office machines
- VDE 0804

Telecommunication apparatus and data processing

IEC60065

Safety for mains-operated electronic and related household apparatus

- VDE 0700/IEC 60335
- Household equipment
- VDE 0160

Electronic equipment for electrical power installation

 VDE 0750/IEC60601 Medical equipment

#### **FEATURES**

- Rated recurring peak voltage (repetitive)
   V<sub>IORM</sub> = 1450 V<sub>peak</sub>
- Thickness through insulation ≥ 3 mm





 Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### **APPLICATIONS**

Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):

- for appl. class I IV at mains voltage ≤ 300 V
- for appl. class I IV at mains voltage ≤ 600 V
- for appl. class I III at mains voltage ≤ 1000 V according to DIN EN 60747-5-2 (VDE 0884), suitable for:
- Switch-mode power supplies
- Line receiver
- Computer peripheral interface
- Microprocessor system interface

#### **AGENCY APPROVALS**

- UL1577, file no. E76222 system code H, J, and K
- DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-5-5 (pending), available with option 1
- VDE related features:
  - rated impulse voltage (transient overvoltage),  $V_{\text{IOTM}} = 12 \text{ kV peak}$
- isolation test voltage (partial discharge test voltage),  $V_{\rm pd} = 2.8 \; \text{kV}$  peak

ORDERING INFORMATION							
C N Y G	PACKAGE CTR OPTION BIN	DIP, 400 mil DIP, 600 mil DIP,					
AGENCY CERTIFIED/PACKAGE		CTR (%)					
UL, VDE	50 to 300	63 to 125	100 to 200				
DIP-4 HV, 400 mil, high isolation distance	CNY64	CNY64A	CNY64B				
DIP-4 HV, 600 mil, high isolation distance	CNY65	CNY65A	CNY65B				
DIP-4 HV, 700 mil, high isolation distance	CNY66	-	CNY66B				

# **CNY64, CNY65, CNY66**



## Vishay Semiconductors Optocoupler, Phototransistor Output, Very High Isolation Voltage

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V <sub>R</sub>	5	V
Forward current		I <sub>F</sub>	75	mA
Forward surge current	t <sub>p</sub> ≤ 10 μs	I <sub>FSM</sub>	1.5	Α
Power dissipation		P <sub>diss</sub>	120	mW
Junction temperature		Tj	100	°C
OUTPUT	·		<u>.</u>	
Collector emitter voltage		V <sub>CEO</sub>	32	V
Emitter collector voltage		V <sub>ECO</sub>	7	V
Collector current		I <sub>C</sub>	50	mA
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I <sub>CM</sub>	100	mA
Power dissipation		P <sub>diss</sub>	130	mW
Junction temperature		Tj	100	°C
COUPLER			·	
AC isolation test voltage CNY64	t = 1 min	V <sub>ISO</sub>	8200	V <sub>RMS</sub>
DC isolation test voltage CNY65	t = 1 s	V <sub>ISO</sub>	13.9	kV
DC isolation test voltage CNY66	t = 1 s	V <sub>ISO</sub>	13.9	kV
Total power dissipation		P <sub>tot</sub>	250	mW
Ambient temperature range		T <sub>amb</sub>	- 55 to + 85	°C
Storage temperature range		T <sub>stg</sub>	- 55 to + 100	°C
Soldering temperature	2 mm from case, ≤ 10 s	T <sub>sld</sub>	260	°C

#### Note

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not
implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute
maximum ratings for extended periods of the time can adversely affect reliability.

<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward voltage	$I_F = 50 \text{ mA}$	$V_{F}$		1.25	1.6	V		
Junction capacitance	V <sub>R</sub> = 0, f = 1 MHz	C <sub>j</sub>		50		pF		
OUTPUT	OUTPUT							
Collector emitter voltage	I <sub>C</sub> = 1 mA	V <sub>CEO</sub>	32			V		
Emitter collector voltage	I <sub>E</sub> = 100 μA	V <sub>ECO</sub>	7			V		
Collector emitter leakage current	V <sub>CE</sub> = 20 V, I <sub>F</sub> = 0 A	I <sub>CEO</sub>			200	nA		
COUPLER								
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V <sub>CEsat</sub>			0.3	V		
Cut-off frequency	$V_{CE}$ = 5 V, $I_F$ = 10 mA, $R_L$ = 100 $\Omega$	f <sub>c</sub>		110		kHz		
Coupling capacitance	f = 1 MHz	C <sub>k</sub>		0.3		pF		

#### Note

• Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.



## Optocoupler, Phototransistor Output, Vishay Semiconductors Very High Isolation Voltage

CURRENT TRANSFER RATIO (T <sub>amb</sub> = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
I <sub>O</sub> ∕I <sub>F</sub>	V <sub>CE</sub> = 5 V, I <sub>F</sub> = 10 mA	CNY64, CNY65, CNY66	CTR	50		300	%	
		CNY64A	CTR	63		125	%	
		CNY65A	CTR	63		125	%	
		CNY64B	CTR	100		200	%	
		CNY65B	CTR	100		200	%	
		CNY66B	CTR	100		200	%	

SAFETY AND INSULATION RATED PARAMETERS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Partial discharge test voltage - routine test	100 %, t <sub>test</sub> = 1 s	V <sub>pd</sub>	2.8			kV	
Partial discharge test voltage - lot test (sample test)	$t_{Tr} = 60 \text{ s}, t_{test} = 10 \text{ s},$ (see fig. 2)	V <sub>pd</sub>	2.2			kV	
Insulation resistance	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 25 °C	R <sub>IO</sub>	10 <sup>12</sup>			Ω	
	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 100 °C	R <sub>IO</sub>	10 <sup>11</sup>			Ω	
	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 150 °C (construction test only)	R <sub>IO</sub>	10 <sup>9</sup>			Ω	
Forward current		I <sub>SI</sub>			120	mA	
Power dissipation		P <sub>SO</sub>			250	mW	
Rated impulse voltage		V <sub>IOTM</sub>			12	kV	
Safety temperature		T <sub>SI</sub>			150	°C	

#### Note

According to DIN EN 60747-5-2 (see fig. 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance
with the safety ratings shall be ensured by means of suitable protective circuits.

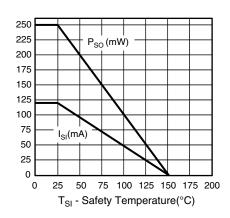


Fig. 1 - Safety Derating Diagram

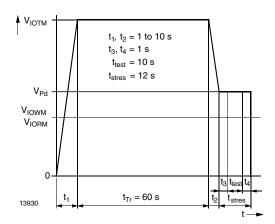


Fig. 2 - Test Pulse Diagram for Sample Test According to DIN EN 60747-5-2 (VDE 0884); IEC60747-5-5



## Vishay Semiconductors Optocoupler, Phototransistor Output, Very High Isolation Voltage

<b>SWITCHING CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Delay time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega, \text{ (see fig. 3)}$	t <sub>d</sub>		2.6		μs	
Rise time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega, \text{ (see fig. 3)}$	t <sub>r</sub>		2.4		μs	
Fall time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega, \text{ (see fig. 3)}$	t <sub>f</sub>		2.7		μs	
Storage time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega, \text{ (see fig. 3)}$	ts		0.3		μs	
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega, \text{ (see fig. 3)}$	t <sub>on</sub>		5		μs	
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega, \text{ (see fig. 3)}$	t <sub>off</sub>		3		μs	
Turn-on time	$V_S = 5 \text{ V}$ , $I_F = 10 \text{ mA}$ , $R_L = 1 \text{ k}\Omega$ , (see fig. 4)	t <sub>on</sub>		25		μs	
Turn-off time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega, \text{ (see fig. 4)}$	t <sub>off</sub>		42.5		μs	

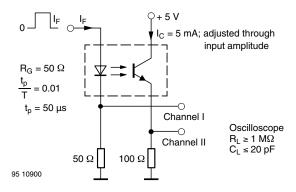


Fig. 3 - Test Circuit, Non-Saturated Operation

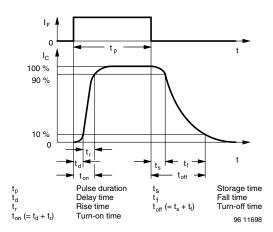


Fig. 5 - Switching Times

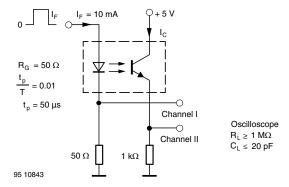


Fig. 4 - Test Circuit, Saturated Operation



## Optocoupler, Phototransistor Output, Vishay Semiconductors Very High Isolation Voltage

## TYPICAL CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

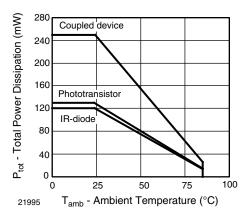


Fig. 6 - Total Power Dissipation vs. Ambient Temperature

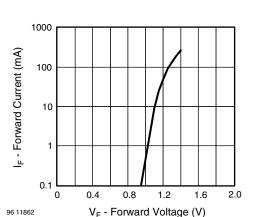


Fig. 7 - Forward Current vs. Forward Voltage

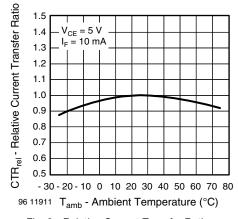


Fig. 8 - Relative Current Transfer Ratio vs.
Ambient Temperature

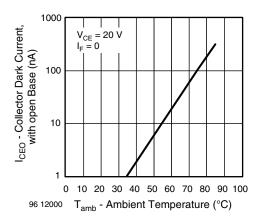


Fig. 9 - Collector Dark Current vs. Ambient Temperature

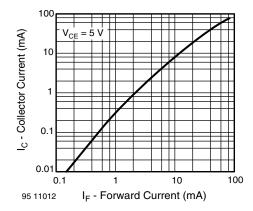


Fig. 10 - Collector Current vs. Forward Current

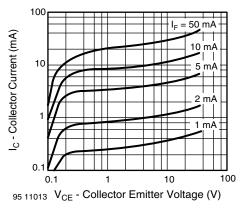


Fig. 11 - Collector Current vs. Collector Emitter Voltage

# Vishay Semiconductors Optocoupler, Phototransistor Output, Very High Isolation Voltage



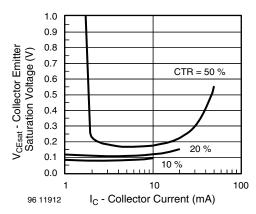


Fig. 12 - Collector Emitter Saturation Voltage vs. Collector Current

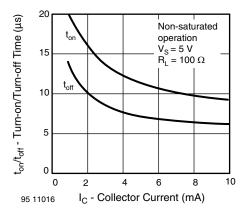


Fig. 15 - Turn-on/Turn-off Time vs. Forward Current

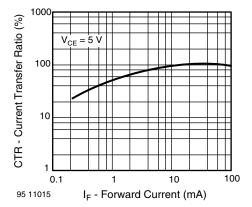


Fig. 13 - Current Transfer Ratio vs. Forward Current

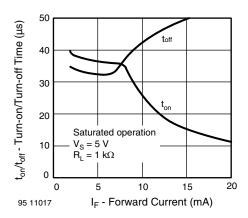


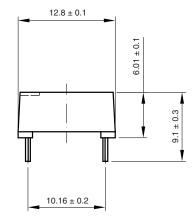
Fig. 14 - Turn-on/Turn-off Time vs. Collector Current

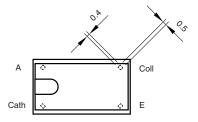


## Optocoupler, Phototransistor Output, Vishay Semiconductors Very High Isolation Voltage

 $7.2 \pm 0.1$ 

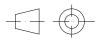
### **PACKAGE DIMENSIONS** in millimeters **FOR CNY64**





Weight: ca. 0.73 g Creepage distance: > 9.5 mm Air path: > 9.5 mm after mounting on PC board

 $5.08 \pm 0.2$ 



technical drawings according to DIN specifications

Drawing-No.: 6.544-5038.01-4

Issue: 2; 10.11.98

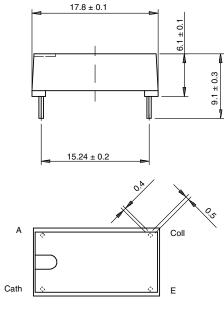
14765

# **CNY64, CNY65, CNY66**

## Vishay Semiconductors Optocoupler, Phototransistor Output, Very High Isolation Voltage



#### **PACKAGE DIMENSIONS** in millimeters FOR CNY65



Drawing-No.: 6.544-5036.01-1 Issue: 2; 10.11.98 9.6 ± 0.1

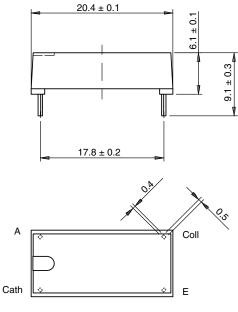
7.62 ± 0.2

Weight: ca. 1.40 g Creepage distance: > 14 mm Air path: > 14 mm

after mounting on PC board

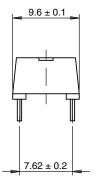


## **PACKAGE DIMENSIONS** in millimeters **FOR CNY66**



Drawing-No.: 6.544-5037.01-4 Issue: x; 10.11.98

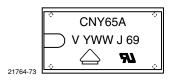
14764



Weight: ca. 1.70 g Creepage distance: > 17 mm Air path: > 17 mm after mounting on PC board



## **PACKAGE MARKING**





## **Legal Disclaimer Notice**

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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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Revision: 02-Oct-12 Document Number: 91000